

Mechanical pressing method for making high-quality perovskite single crystals

Chenglin Wang¹, Jie Sun³, Jiangzhao Chen^{2,†}, Cong Chen^{1,4,†}, and Liming Ding^{3,†}

¹State Key Laboratory of Reliability and Intelligence of Electrical Equipment, School of Materials Science and Engineering, Hebei University of Technology, Tianjin 300401, China

²Faculty of Materials Science and Engineering, Kunming University of Science and Technology, Kunming 650093, China

³Center for Excellence in Nanoscience (CAS), Key Laboratory of Nanosystem and Hierarchical Fabrication (CAS), National Center for Nanoscience and Technology, Beijing 100190, China

⁴Macao Institute of Materials Science and Engineering (MIMSE), Macau University of Science and Technology, Macau 999078, China

Citation: C L Wang, J Sun, J Z Chen, C Chen, and L M Ding, Mechanical pressing method for making high-quality perovskite single crystals[J]. *J. Semicond.*, 2023, 44(11), 110201. <https://doi.org/10.1088/1674-4926/44/11/110201>

Halide perovskites show excellent photovoltaic properties^[1–4]. However, the preparation of high-quality perovskite crystals remains a great challenge, which limits their applications. Perovskite materials applied to photodetectors mainly include polycrystalline thin films and single crystals. Traditional solution methods are used to prepare polycrystalline thin films, and the films are full of defects such as voids and grain boundaries^[5–7]. Compared to polycrystalline thin films, perovskite single crystals possess high crystallinity and low defect density^[8–10]. Photodetectors based on perovskite single crystals exhibit excellent performance^[11]. However, the size limitation of single crystals hinders their application in photodetectors^[12].

There are several reports on perovskite quasi-single crystal wafers for photodetectors, which show low defect density and good performance^[13–16]. The soft lattice of perovskite allows perovskite powder to be sufficiently deformed and densified under low pressure^[17, 18]. Shrestha *et al.* used a mechanical pressing process to make polycrystalline MAPbI₃ wafer with millimeter thickness and high crystallinity (Fig. 1(a))^[13]. They made MAPbI₃ wafers by applying a pressure of 0.3 GPa for 5 min to the microcrystals precipitated from solution. The wafer was then pressed onto PEDOT substrate under a pressure of 15 MPa for 2 min, thus obtaining an X-ray detector (Fig. 1(b)). The device exhibited a sensitivity of 2527 $\mu\text{C}/(\text{Gy}_{\text{air}}\cdot\text{cm}^2)$ under 70 kV_p X-ray exposure (Fig. 1(c)).

In addition to applying a stress field to the microcrystals/powder from perovskite precursor, a secondary coupling effect can be triggered. The direct densification of perovskite from powder to high-quality bulk crystals can be achieved in minutes under the dual action of a stress field and a thermal/electric field. Hu *et al.* prepared large MAPbI₃ wafers (diameter ~80 mm) from perovskite powder by heat-assisted pressing method^[19]. The X-ray detector with MAPbI₃ wafers has an X-ray sensitivity of $1.22 \times 10^5 \mu\text{C}/(\text{Gy}_{\text{air}}\cdot\text{cm}^2)$ at 10 V bias. Zheng *et al.* first reported an electric and mechanical field-assisted sintering technique (EM-FAST) for making per-

ovskite wafers, which can produce high-quality bulk crystals in 5 min (Fig. 1(d))^[16]. The pressure leads to better contact between the particles, thus forming a sintered neck. The small contact area at the sintered neck leads to an increase in local pressure, which triggers grain boundary diffusion and sliding. Moreover, localized thermal concentration is induced at the neck under the application of electric field, and this surface heating triggers mass transfer and grain integration. A very dense bulk crystal was obtained by using the FAST method. The optical bandgap of FAST product (1.45 eV) is close to that of the single crystal (1.51 eV) (Fig. 1(e)). The defect density of FAST product reaches $5.4 \times 10^{10} \text{cm}^{-3}$, which is close to that of the single crystal (Fig. 1(f)).

The same passivation strategies applied in solution engineering can also be applied to mechanical pressing methods. Yang *et al.* introduced a bismuth oxybromide (BiOBr) heteroepitaxial passivation layer in Cs₂AgBiBr₆ polycrystalline wafers (Figs. 2(a) and 2(b))^[14]. BiOBr initiated the epitaxial growth of Cs₂AgBiBr₆ grain boundaries, resulting in a grain size of 100 μm while passivating the grain boundary defects and eliminating the ion migration. The detector showed improved stability with a sensitivity of 250 $\mu\text{C}/(\text{Gy}_{\text{air}}\cdot\text{cm}^2)$ (Fig. 2(c)).

Witt *et al.* investigated the factors such as pressure, pressing time and temperature during the pressing process^[15]. Above 35 °C, rapid compression occurred, mainly due to two relaxation processes caused by plastic deformation and particle rearrangement. The optimal pressing conditions (100 MPa, 100 °C, 130 min) yield MAPbI₃ wafers with relative density >97%, high crystallinity, and an average size of 1.9 μm . Besides X-ray detectors, perovskite wafers can also be used in near-infrared detectors. Yu *et al.* made dense and smooth MAPbI₃ wafers from MAPbI₃ single crystals by hot pressing method^[20]. The near-infrared detector exhibited a responsivity of 2.1 A·W⁻¹ (Fig. 2(d)), rise and decay time of ~239 μs and ~6.13 ms (Fig. 2(e)), and high cycling stability (Fig. 2(f)).

Most photodetectors are made from polycrystalline films or single crystals of perovskite^[21–23]. All efforts focus on defect passivation^[24, 25], interface modification^[26, 27] and film formation control^[28] of polycrystalline thin films as well as crystallization engineering of single crystals. Mechanical pressing method is an easy and fast process for preparing perovskite bulk crystals. It is also necessary to achieve high adhesion

Correspondence to: J Z Chen, jiangzhaochen@cqu.edu.cn; C Chen, chencong@hebut.edu.cn; L M Ding, ding@nanoctr.cn

Received 25 SEPTEMBER 2023.

©2023 Chinese Institute of Electronics

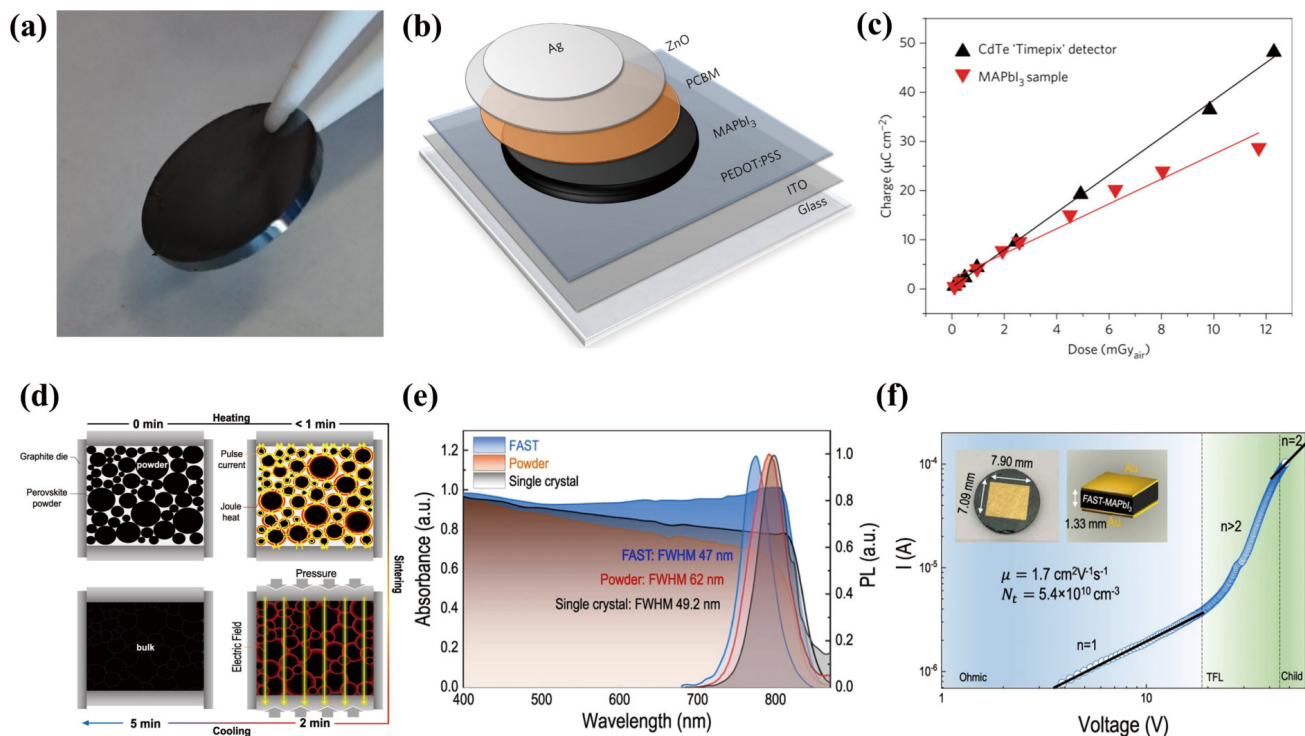


Fig. 1. (Color online) (a) The sintered MAPbI₃ wafer. (b) The X-ray detector with MAPbI₃ wafer. (c) Extracted charge at $E = 0.2 \text{ V} \cdot \mu\text{m}^{-1}$ for MAPbI₃-wafer-based device and CdTe reference detector. All exposures are 2-s-long pulses from an X-ray source operated at 70 kV. Reproduced with permission^[13], Copyright 2017, Nature Publishing Group. (d) Densification of perovskites in graphite die. (e) UV-vis absorption and steady-state PL spectra for FAST-MAPbI₃ and MAPbI₃ powder. (f) I - V curve for the hole-only device under dark. Reproduced with permission^[16], Copyright 2016, Nature Publishing Group.

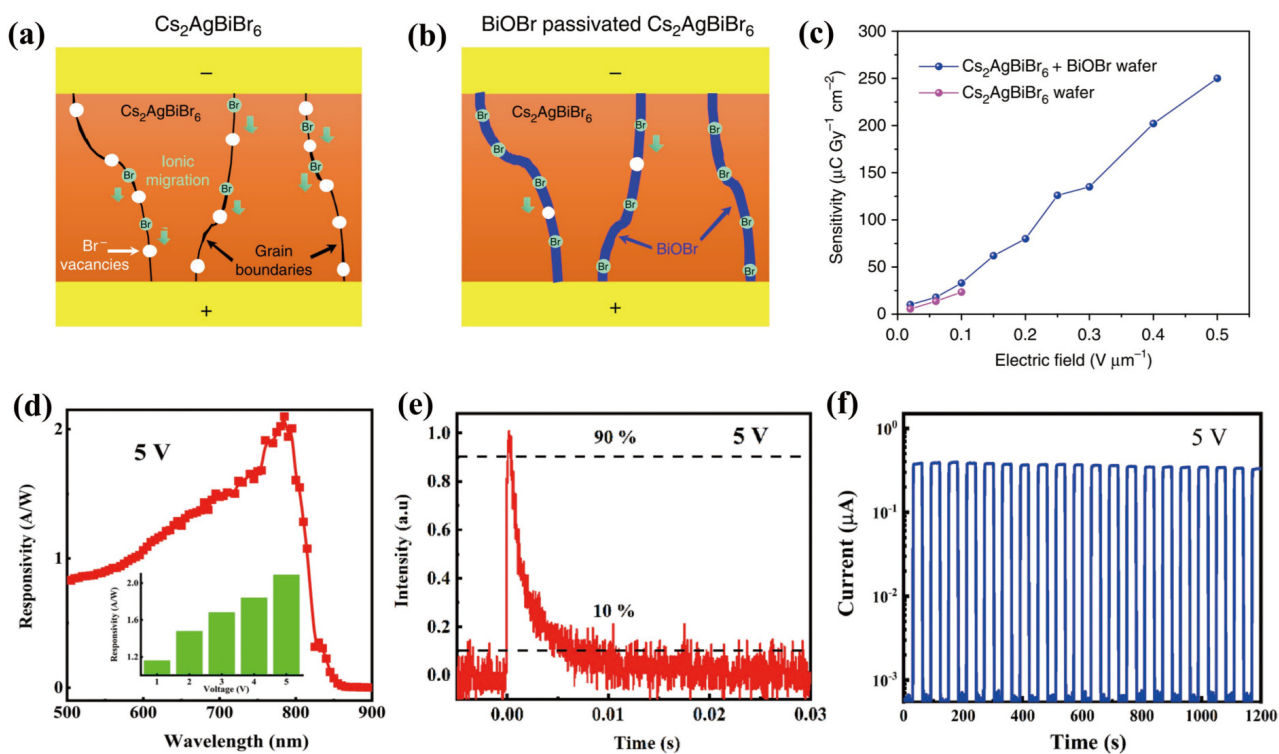


Fig. 2. (Color online) (a) Ion migration. (b) Suppressed ion migration by BiOBr passivation. (c) X-ray sensitivity under different electric fields. Reproduced with permission^[14], Copyright 2019, Nature Publishing Group. (d) Photoresponse spectrum for the photodetector at 5 V. (e) Response time of the photodetector at 5 V. (f) Photocurrent of the photodetector as a function of time measured during periodical switching of 800 nm light illumination at 5 V. Reproduced with permission^[20], Copyright 2023, Royal Society of Chemistry.

between perovskite wafers and the underlying substrate. We should explore the adaptability of perovskite materials with

other materials (metals^[29], carbon^[30], 2D materials^[31], etc.) to improve device performance.

Acknowledgements

This work was supported by the National Natural Science Foundation of China (62004058 and U21A2076), Natural Science Foundation of Hebei Province (F2020202022), State Key Laboratory of Reliability and Intelligence of Electrical Equipment (EERI_PI20200005), S&T Program of Hebei (215676146H and 225676163GH), and Hebei Graduate Innovation Funding Project (CXZZBS2023037 and CXZZSS2023026). L. Ding thanks the National Key Research and Development Program of China (2022YFB3803300), the open research fund of Songshan Lake Materials Laboratory (2021SLABFK02), and the National Natural Science Foundation of China (21961160720).

References

- [1] Zhu L H, Zhang X, Li M J, et al. Trap state passivation by rational ligand molecule engineering toward efficient and stable perovskite solar cells exceeding 23% efficiency. *Adv Energy Mater*, 2021, 11, 2100529
- [2] Gao D Y, Li R, Chen X H, et al. Managing interfacial defects and carriers by synergistic modulation of functional groups and spatial conformation for high-performance perovskite photovoltaics based on vacuum flash method. *Adv Mater*, 2023, 35, 2301028
- [3] Zhao Y, Ma F, Qu Z H, et al. Inactive (PbI₂)₂RbCl stabilizes perovskite films for efficient solar cells. *Science*, 2022, 377, 531
- [4] Park J, Kim J, Yun H S, et al. Controlled growth of perovskite layers with volatile alkylammonium chlorides. *Nature*, 2023, 616, 724
- [5] Wu H R, Su Z S, Jin F M, et al. Improved performance of perovskite photodetectors based on a solution-processed CH₃NH₃PbI₃/SnO₂ heterojunction. *Org Electron*, 2018, 57, 206
- [6] Yin W J, Shi T T, Yan Y F. Unusual defect physics in CH₃NH₃PbI₃ perovskite solar cell absorber. *Appl Phys Lett*, 2014, 104, 063903
- [7] Ono L K, Liu S Z, Qi Y B. Reducing detrimental defects for high-performance metal halide perovskite solar cells. *Angew Chem Int Ed*, 2020, 59, 6676
- [8] Bao C X, Chen Z L, Fang Y J, et al. Low-noise and large-linear-dynamic-range photodetectors based on hybrid-perovskite thin-single-crystals. *Adv Mater*, 2017, 29, 1703209
- [9] Zhang Y X, Liu Y C, Yang Z, et al. High-quality perovskite MAPbI₃ single crystals for broad-spectrum and rapid response integrate photodetector. *J Energy Chem*, 2018, 27, 722
- [10] Ding J, Fang H J, Lian Z P, et al. A self-powered photodetector based on a CH₃NH₃PbI₃ single crystal with asymmetric electrodes. *Cryst Eng Comm*, 2016, 18, 4405
- [11] Yu J, Zheng J, Chen H Y, et al. Near-infrared photodetectors based on CH₃NH₃PbI₃ perovskite single crystals for bioimaging applications. *J Mater Chem C*, 2022, 10, 274
- [12] Leupold N, Panzer F. Recent advances and perspectives on powder-based halide perovskite film processing. *Adv Funct Mater*, 2021, 31, 2007350
- [13] Shrestha S, Fischer R, Matt G J, et al. High-performance direct conversion X-ray detectors based on sintered hybrid lead triiodide perovskite wafers. *Nat Photonics*, 2017, 11, 436
- [14] Yang B, Pan W C, Wu H D, et al. Heteroepitaxial passivation of Cs₂AgBiBr₆ wafers with suppressed ionic migration for X-ray imaging. *Nat Commun*, 2019, 10, 1989
- [15] Witt C, Schmid A, Leupold N, et al. Impact of pressure and temperature on the compaction dynamics and layer properties of powder-pressed methylammonium lead halide thick films. *ACS Appl Electron Mater*, 2020, 2, 2619
- [16] Zheng L Y, Nozariasbmarz A, Hou Y C, et al. A universal all-solid synthesis for high throughput production of halide perovskite. *Nat Commun*, 2022, 13, 7399
- [17] Bonn M, Miyata K, Hendry E, et al. Role of dielectric drag in polaron mobility in lead halide perovskites. *ACS Energy Lett*, 2017, 2, 2555
- [18] Skrotzki W, Frommeyer O, Haasen P. Plasticity of polycrystalline ionic solids. *Phys Status Solidi A*, 1981, 66, 219
- [19] Hu M X, Jia S S, Liu Y C, et al. Large and dense organic-inorganic hybrid perovskite CH₃NH₃PbI₃ wafer fabricated by one-step reactive direct wafer production with high X-ray sensitivity. *ACS Appl Mater Interfaces*, 2020, 12, 16592
- [20] Yu J, Qu Y M, Deng Y F, et al. Hot-pressed CH₃NH₃PbI₃ polycrystalline wafers for near-infrared bioimaging and medical X-ray imaging. *J Mater Chem C*, 2023, 11, 5815
- [21] Jing H, Peng R W, Ma R M, et al. Flexible ultrathin single-crystalline perovskite photodetector. *Nano Lett*, 2020, 20, 7144
- [22] Sun J, Ding L M. Linearly polarization-sensitive perovskite photodetectors. *Nano-Micro Lett*, 2023, 15, 90
- [23] Cheng Y H, Ding L M. Pushing commercialization of perovskite solar cells by improving their intrinsic stability. *Energy Environ Sci*, 2021, 14, 3233
- [24] Jiang Q, Zhao Y, Zhang X W, et al. Surface passivation of perovskite film for efficient solar cells. *Nat Photonics*, 2019, 13, 460
- [25] Liu X X, Yu Z G, Wang T A, et al. Full defects passivation enables 21% efficiency perovskite solar cells operating in air. *Adv Energy Mater*, 2020, 10, 2001958
- [26] Gao D Y, Yang L Q, Ma X H, et al. Passivating buried interface with multifunctional novel ionic liquid containing simultaneously fluorinated anion and cation yielding stable perovskite solar cells over 23% efficiency. *J Energy Chem*, 2022, 69, 659
- [27] Zuo C T, Ding L M. Modified PEDOT layer makes a 1.52 V V_{oc} for perovskite/PCBM solar cells. *Adv Energy Mater*, 2017, 7, 1601193
- [28] Zuo C T, Ding L M. Drop-casting to make efficient perovskite solar cells under high humidity. *Angew Chem Int Ed*, 2021, 133, 11342
- [29] Liu B, Wang J S, Liu Y, et al. Microstructure and mechanical properties of equimolar FeCoCrNi high entropy alloy prepared via powder extrusion. *Intermetallics*, 2016, 75, 25
- [30] Ibrahim K, Shahin A, Jones A, et al. Humidity-resistant perovskite solar cells via the incorporation of halogenated graphene particles. *Sol Energy*, 2021, 224, 787
- [31] Li X T, Hoffman J M, Kanatzidis M G. The 2D halide perovskite rulebook: How the spacer influences everything from the structure to optoelectronic device efficiency. *Chem Rev*, 2021, 121, 2230



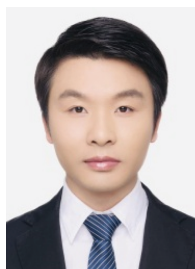
Chenglin Wang got his BE from Hebei University of Technology in June 2020. Now he is a Master student in School of Materials Science and Engineering under the supervision of Prof. Cong Chen at Hebei University of Technology. His research focuses on perovskite solar cells.



Jie Sun got her BS from Minzu University of China in 2021. Now she is a PhD student at University of Chinese Academy of Sciences under the supervision of Prof. Liming Ding. Her research focuses on perovskite devices.



Jiangzhao Chen is a professor at College of Optoelectronic Engineering in Chongqing University. He received PhD from Huazhong University of Science and Technology, and then worked as a postdoc at Sungkyunkwan University and at the University of Hong Kong, respectively. His work focuses on perovskite solar cells.



Cong Chen is currently an associate professor at Hebei University of Technology. He received his PhD from Jilin University in June 2019. His research focuses on solar cells and NIR photodetectors.



Liming Ding got his PhD from University of Science and Technology of China (was a joint student at Changchun Institute of Applied Chemistry, CAS). He started his research on OSCs and PLEDs in Olle Inganäs Lab in 1998. Later on, he worked at National Center for Polymer Research, Wright-Patterson Air Force Base and Argonne National Lab (USA). He joined Konarka as a Senior Scientist in 2008. In 2010, he joined National Center for Nanoscience and Technology as a full professor. His research focuses on innovative materials and devices. He is RSC Fellow, and the Associate Editor for *Journal of Semiconductors*.